2SC5024

Silicon NPN Epitaxial

HITACHI

Application

High frequency amplifier

Features

- Excellent high frequency characteristics f_T = 300 MHz typ
- High breakdown voltage and low output capacitance V_{CEO} = 200 V, Cob = 5.0 pF typ
- Suitable for wide band video amplifier
- Complimentary pair of 2SA1889

Outline

TO-126FM

1. Emitter
2. Collector
3. Base

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Absolute Maximum Ratings (Ta = 25°C)

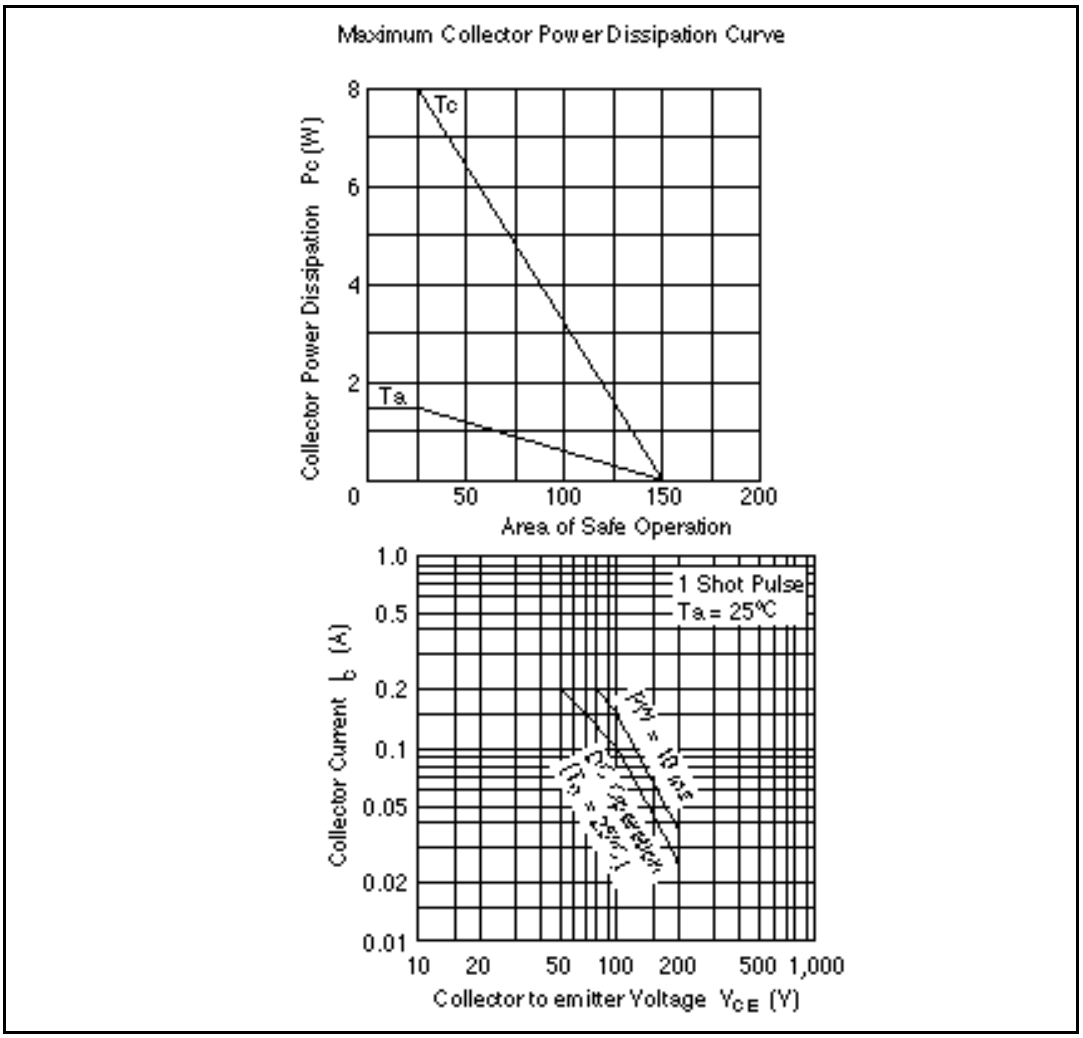
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	200	V
Collector to emitter voltage	V_{CEO}	200	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_C	0.2	A
Collector peak current	$I_{C\ (peak)}$	0.5	A
Collector power dissipation	P_C	1.4	W
	P_C*[1]	8	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

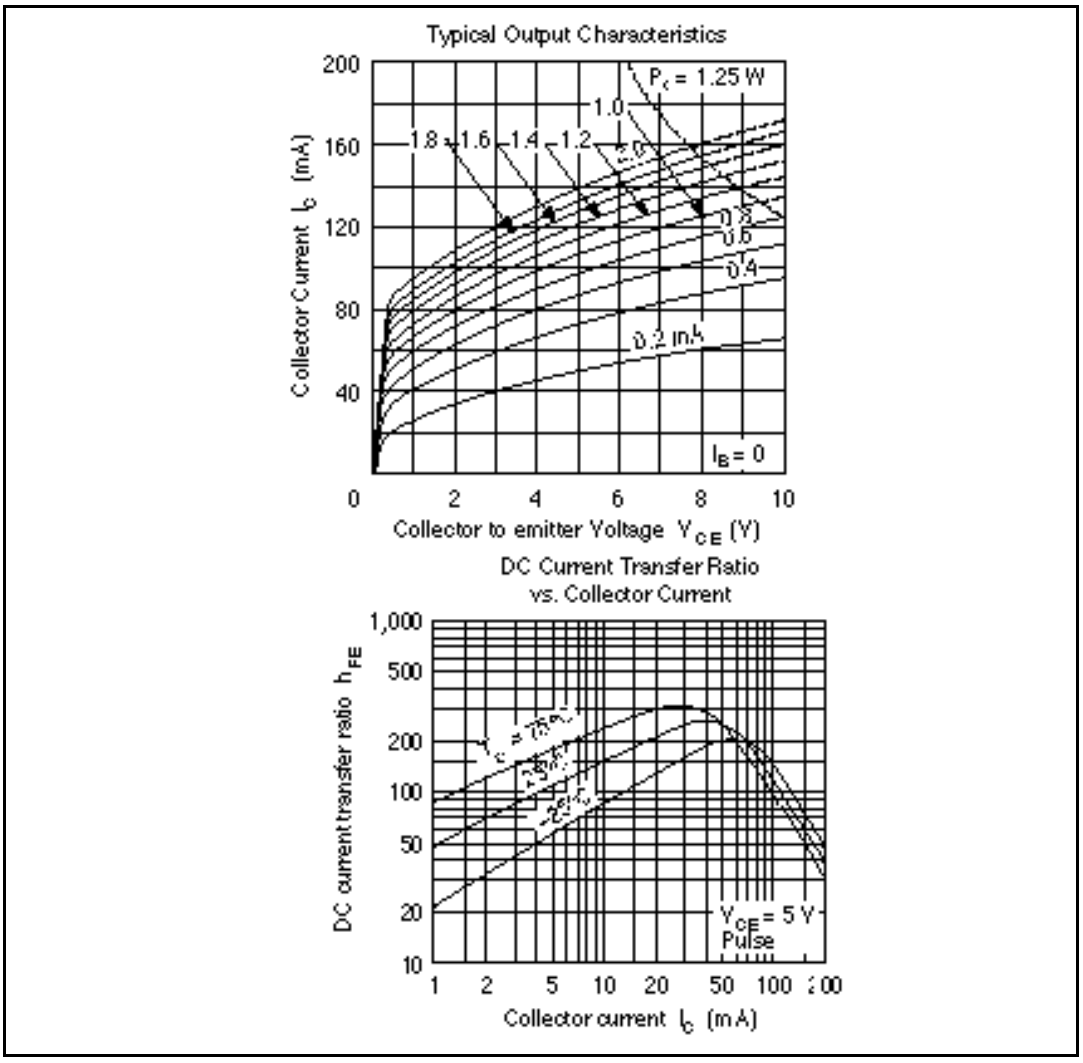
Note: 1. Value at T_C = 25°C.

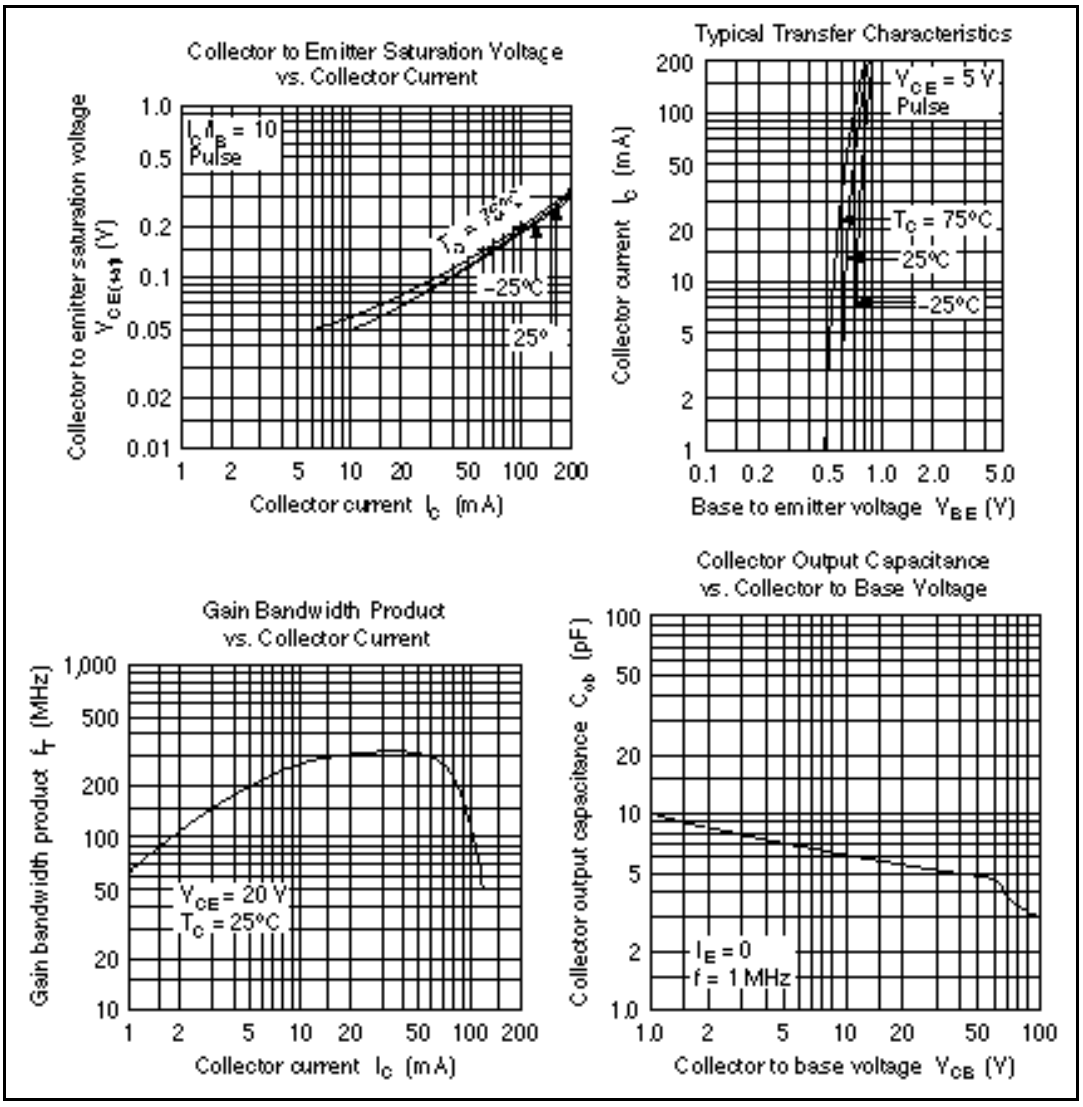
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage		$V_{(BR)CBO}$	200	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage		$V_{(BR)CEO}$	200	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage		$V_{(BR)EBO}$	4	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current		I_{CBO}	—	—	10	µA	V_{CB} = 160 V, I_E = 0
DC current	2SC5024B	h_{FE}	60	—	120		V_{CE} = 5 V, I_C = 10 mA
transfer ratio	2SC5024C	h_{FE}	100	—	200		
Base to emitter voltage		V_{BE}	—	—	1.0	V	V_{CE} = 5 V, I_C = 30 mA
Collector to emitter saturation voltage		$V_{CE\ (sat)}$	—	—	1.0	V	I_C = 30 mA, I_B = 3 mA
Gain bandwidth product		f_T	200	300	—	MHz	V_{CE} = 20 V, I_C = 30 mA
Collector output capacitance		Cob	—	5.0	—	pF	V_{CB} = 30 V, I_E = 0, f = 1 MHz

See characteristic curves of 2SC4704.







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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U.S.A.
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071